

1/8

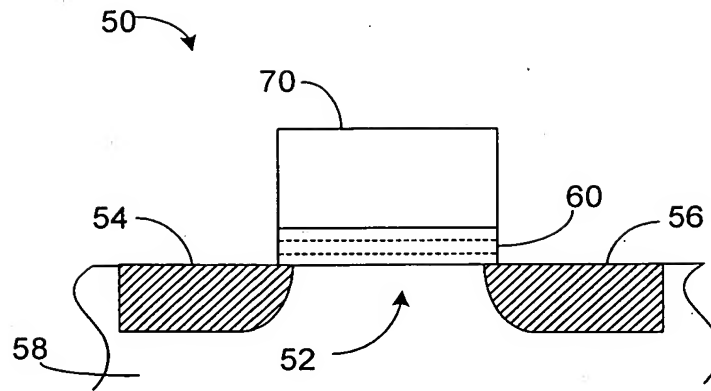


FIG. 1
PRIOR ART

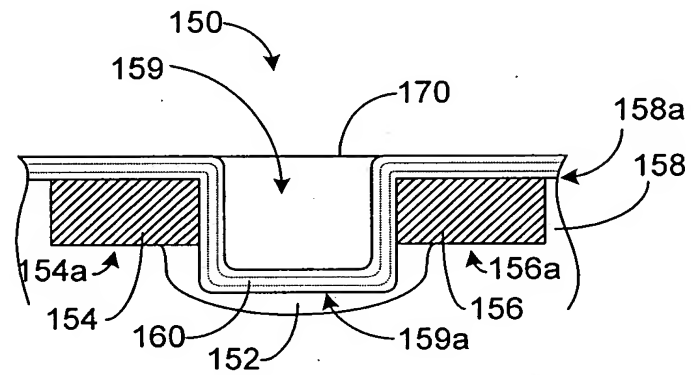


FIG. 2A

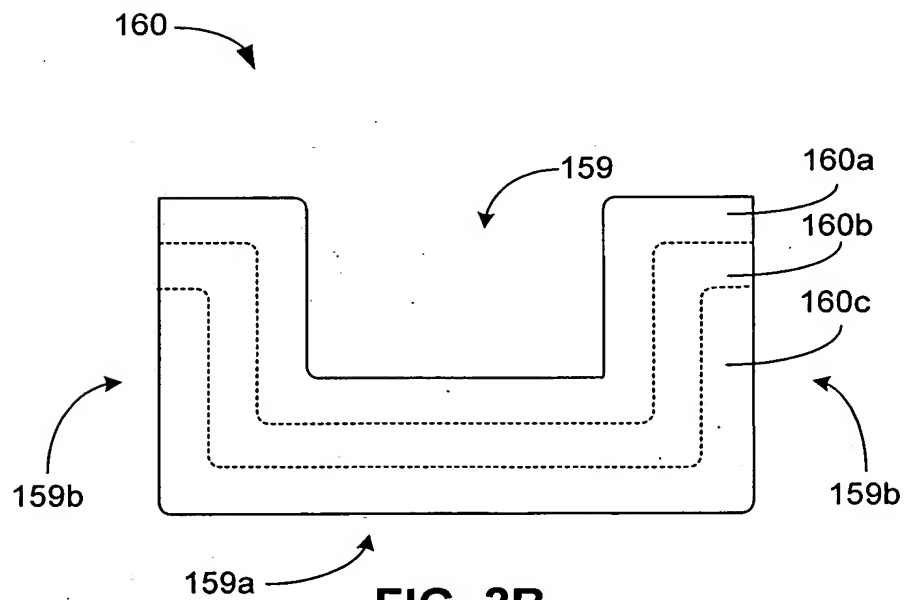
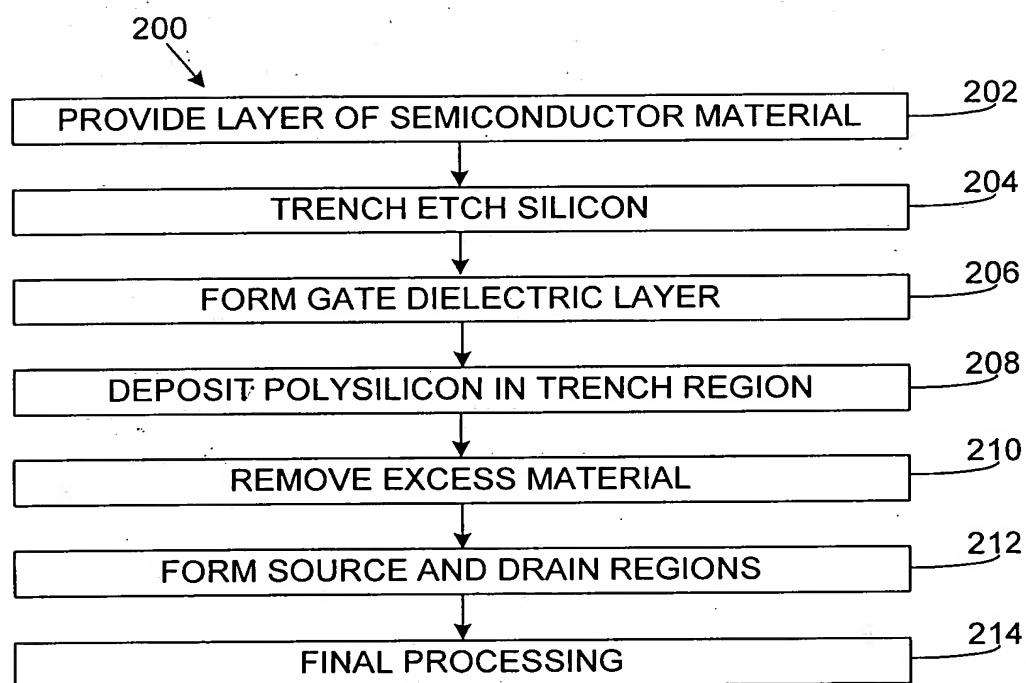


FIG. 2B

**FIG. 3**

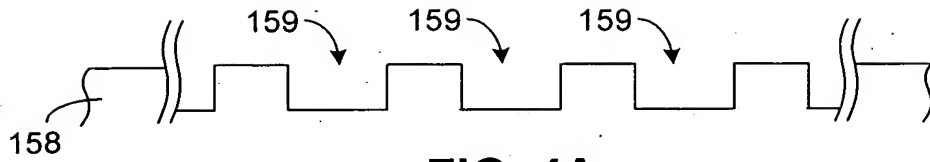


FIG. 4A

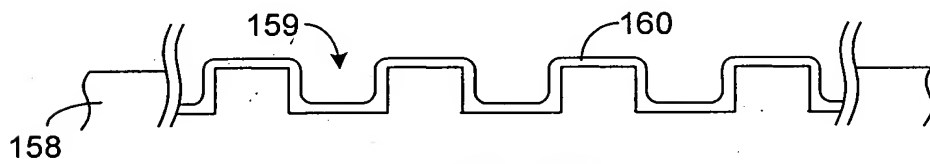


FIG. 4B

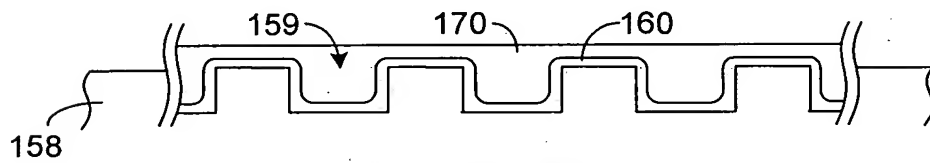


FIG. 4C

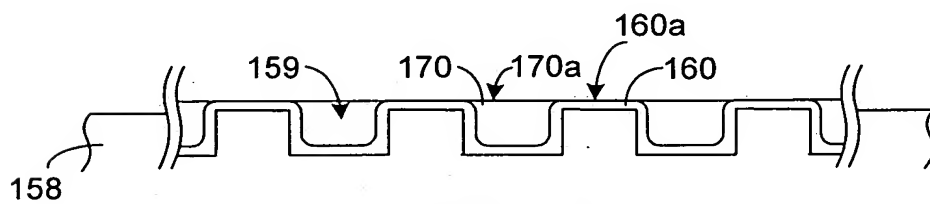


FIG. 4D

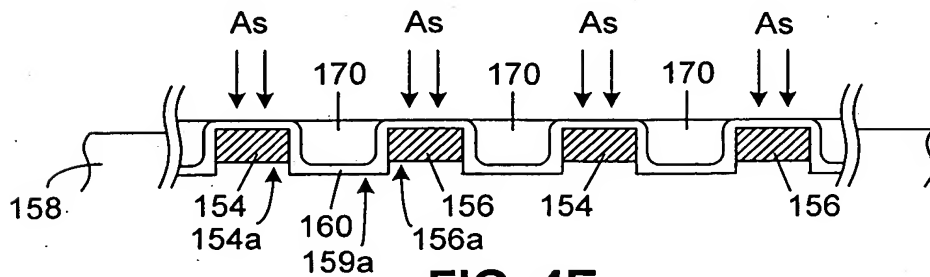


FIG. 4E

A cross-sectional view of a semiconductor device. A central U-shaped well (170) is formed in a substrate (150). The well is lined with a material (172a, 172b) and has a bottom layer (152). The well is surrounded by a layer (160) which is divided into regions 160b and 160c. A layer (154) is on the left, and a layer (156) is on the right. A region (158) is indicated by a dashed line. A region (159) is indicated by a circle with 'hh' inside. A region (161) is indicated by a circle with 'V+' inside. A region (162) is indicated by a circle with 'V-' inside.

FIG. 5

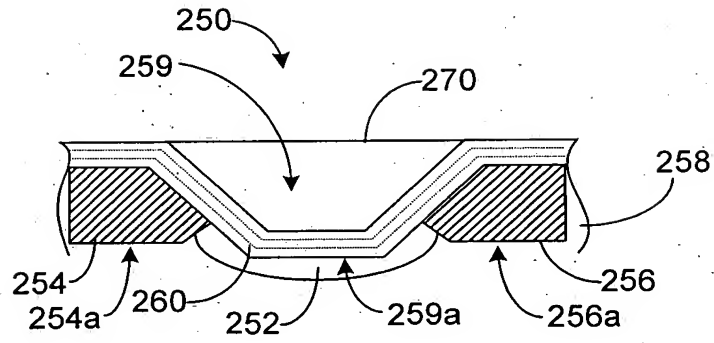


FIG. 6A

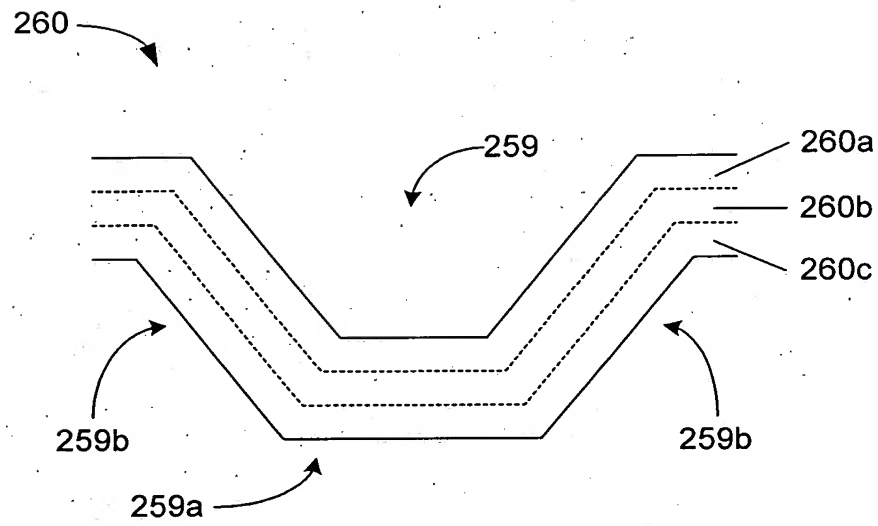
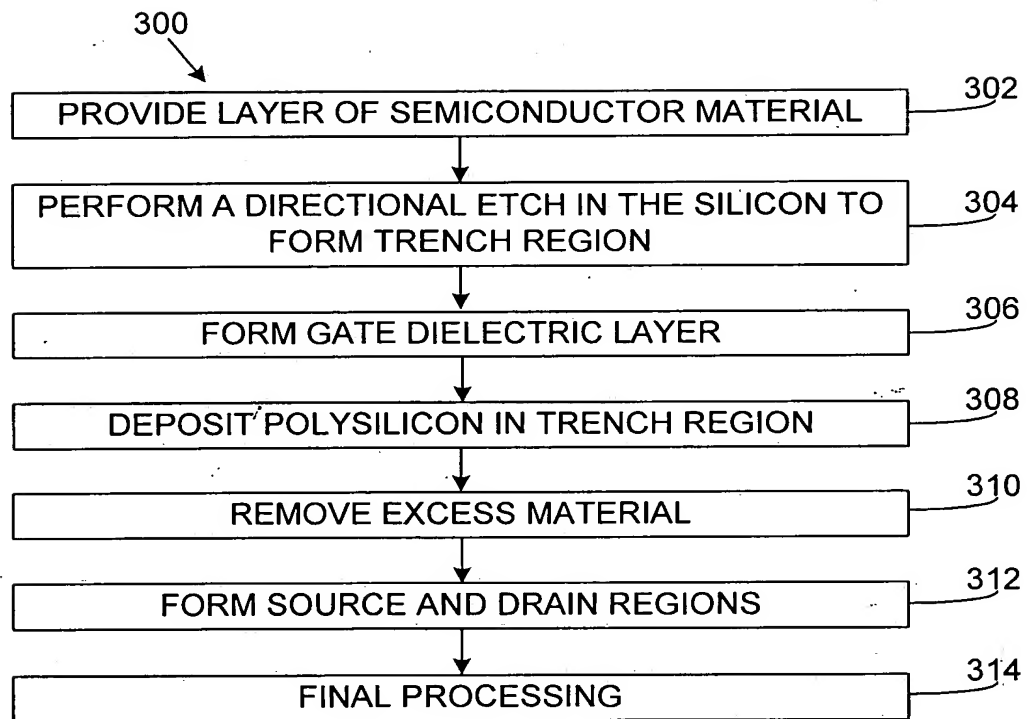


FIG. 6B

**FIG. 7**

7/8

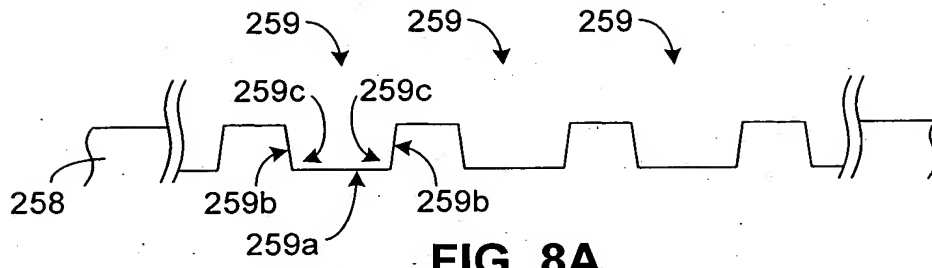


FIG. 8A

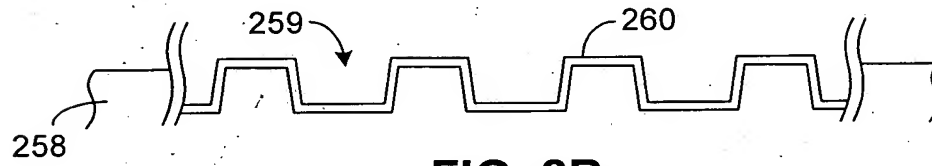


FIG. 8B

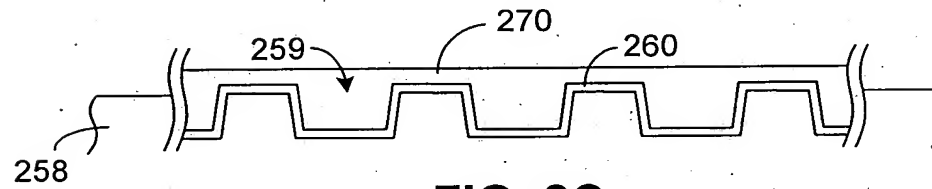


FIG. 8C

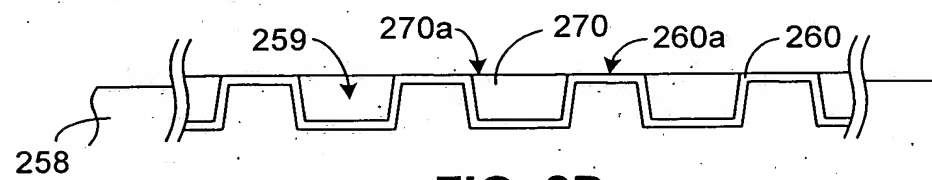


FIG. 8D

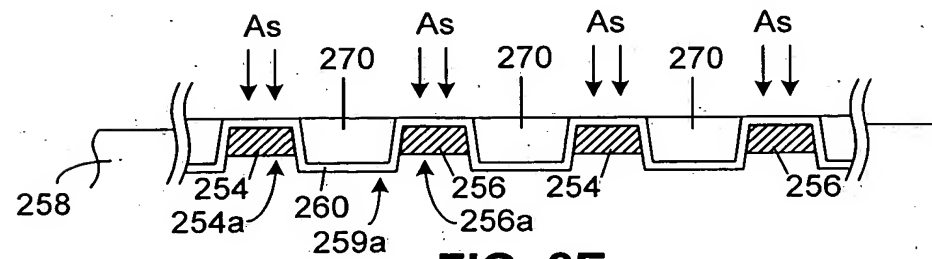


FIG. 8E

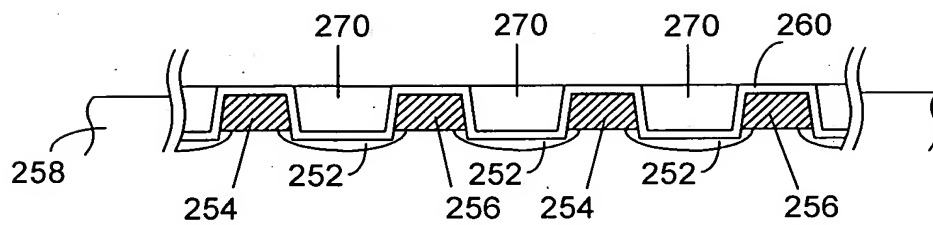


FIG. 8F